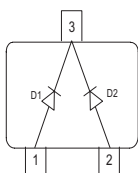


Silicon Variable Capacitance Diode

- For FM radio tuner with extended frequency band
- High tuning ratio at low supply voltage (car radio)
- Monolithic chip (common cathode) for perfect dual diode tracking
- Good linearity for C- V curve
- High figure of merit
- Pb-free (RoHS compliant) package



BB914



Type	Package	Configuration	L_S (nH)	Marking
BB914	SOT23	common cathode	1.8	SM

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	18	V
Peak reverse voltage ($R \geq 5\text{k}\Omega$)	V_{RM}	20	
Forward current	I_F	50	mA
Operating temperature range	T_{op}	-55 ... 125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ... 150	

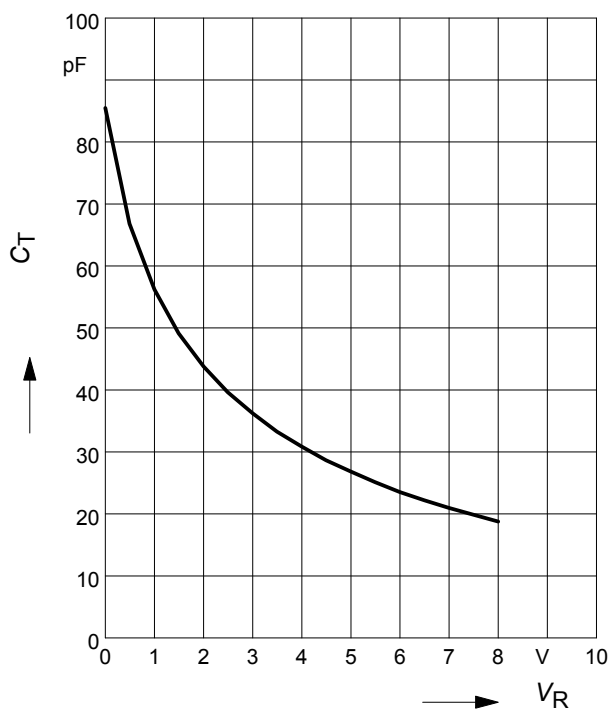
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current $V_R = 16\text{ V}$ $V_R = 16\text{ V}, T_A = 85\text{ }^{\circ}\text{C}$	I_R	- -	- -	20 200	nA
AC Characteristics					
Diode capacitance $V_R = 2\text{ V}, f = 1\text{ MHz}$ $V_R = 8\text{ V}, f = 1\text{ MHz}$	C_T	42.5 17.6	43.75 18.7	45 19.75	pF
Capacitance ratio $V_R = 2\text{ V}, V_R = 8\text{ V}, f = 1\text{ MHz}$	C_{T2}/C_{T8}	2.28	2.34	2.42	
Capacitance matching ¹⁾ $V_R = 2\text{ V}, V_R = 8\text{ V}, f = 1\text{ MHz}$	$\Delta C_T/C_T$	-	-	1.5	%
Series resistance $V_R = 2\text{ V}, f = 100\text{ MHz}$	r_S	-	0.28	-	Ω

¹For details please refer to Application Note 047.

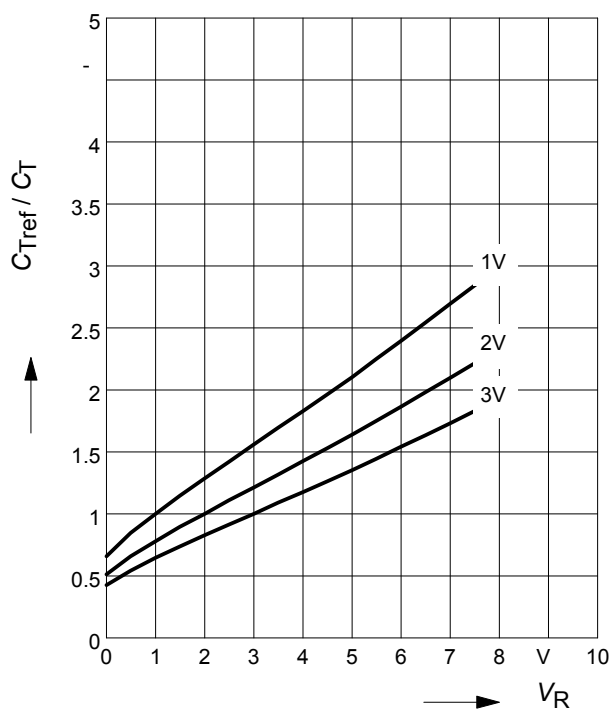
Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$

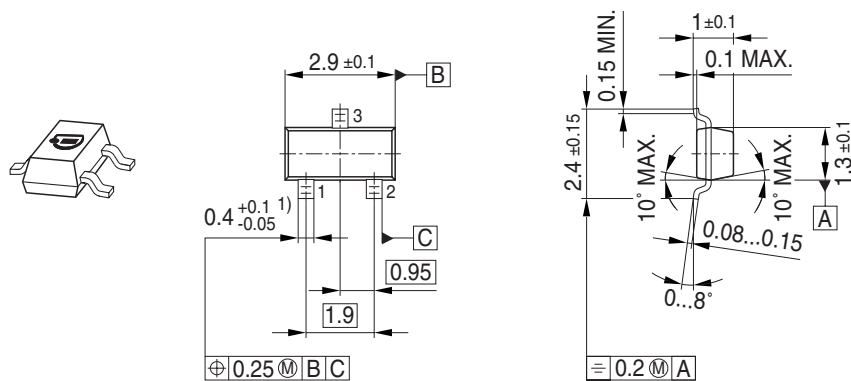


Capacitance ratio $C_{Tref}/C_T = f(V_R)$

$f = 1\text{MHz}$

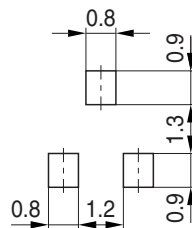


Package Outline

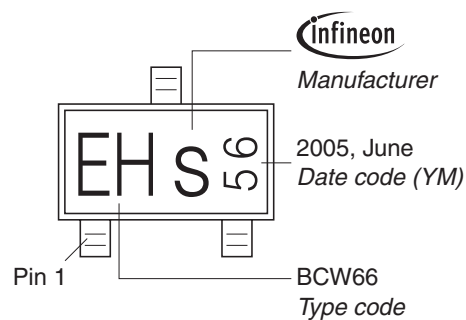


1) Lead width can be 0.6 max. in dambar area

Foot Print

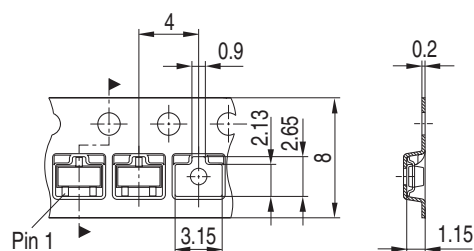


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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